AP70P03D

-30V P-Channel Enhancement Mode MOSFET

Description

The AP70P03D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

V_{DS} = -30V I_D =-70A

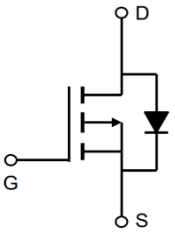
$R_{DS(ON)}$ <9.0mΩ @ V_{GS}=-10V （**Type：6.5mΩ**）

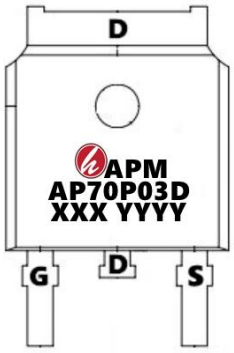
Application

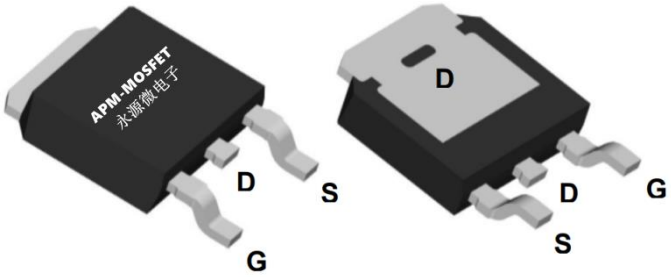
Lithium battery protection

Wireless impact

Mobile phone fast charging







Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP70P03D	TO-252-3L	AP70P03D XXX YYYY	5000

Absolute Maximum Ratings (TC=25℃unless otherwise noted)

Symbol	Parameter	Max.	Units
VDSS	Drain-Source Voltage	-30	V
VGSS	Gate-Source Voltage	±20	V
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ -10V[1]	70	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ -10V[1]	50	A
IDM	Pulsed Drain Current note1	-220	A
EAS	Single Pulsed Avalanche Energy note2	121	mJ
P_D@T_A=25℃	Power Dissipation	65.2	W
RθJC	Thermal Resistance, Junction to Case	2.9	℃/W
TJ, TSTG	Operating and Storage Temperature Range	-55 to +175	℃

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Electrical Characteristics (T_J=25℃, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D= -250μA	-30	33	-	V
IDSS	Zero Gate Voltage Drain Current	V_{DS}= -30V, V_{GS}=0V,	-	-	-1	μA
IGSS	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}= ±20V	-	-	±100	nA
VGS(th)	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D= -250μA	-1.0	-1.6	-2.5	V
RDS(on)	Static Drain-Source on-Resistance note3	V_{GS}= -10V, I_D= -30A	-	6.5	9.0	mΩ
		V_{GS}= -4.5V, I_D= -20A	-	11.6	16	
C_{iss}	Input Capacitance	V_{DS}= -15V, V_{GS}=0V, f=1.0MHz	-	3564	-	pF
Coss	Output Capacitance		-	416	-	pF
Crss	Reverse Transfer Capacitance		-	373	-	pF
Q_g	Total Gate Charge	V_{DS}= -15V, I_D= -20A, V_{GS}= -10V	-	37	-	nC
Q_{gs}	Gate-Source Charge		-	6.5	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	9.4	-	nC
td(on)	Turn-on Delay Time	V_{DD}= -15V, I_D= -30A, V_{GS}= -10V, R_{GEN}=2.5Ω	-	16	-	ns
t_r	Turn-on Rise Time		-	21	-	ns
td(off)	Turn-off Delay Time		-	68	-	ns
t_f	Turn-off Fall Time		-	52	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	-55	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-220	A
VSD	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S= -30A	-	-0.8	-1.2	V

Note :

1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width .The EAS data shows Max. rating .

3、The power dissipation is limited by 175℃ junction temperature

4、EAS condition: TJ=25℃, VDD= -15V, VG= -10V, RG=25Ω, L=0.5mH, IAS= -22A

5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

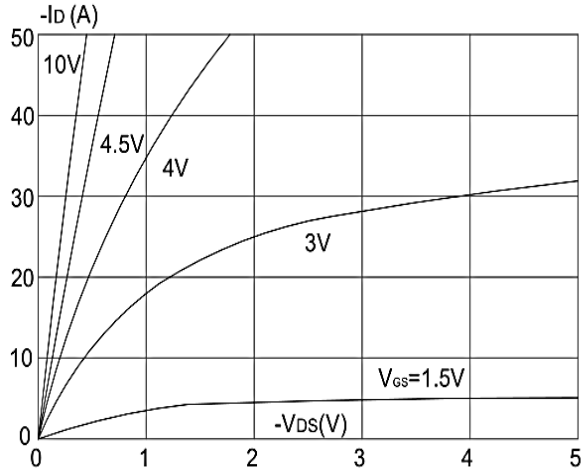


Figure1: Output Characteristics Figure

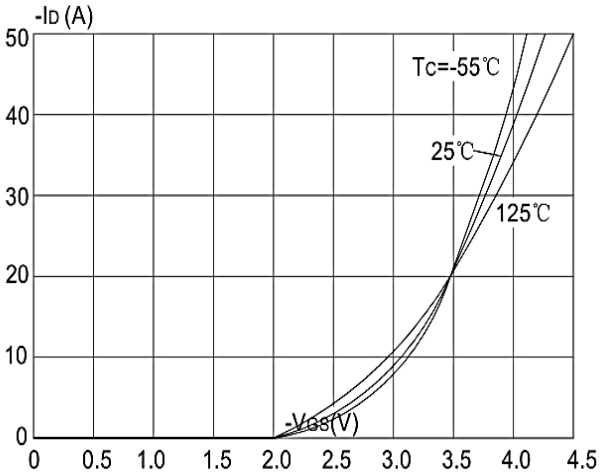


Figure2: Typical Transfer Characteristics

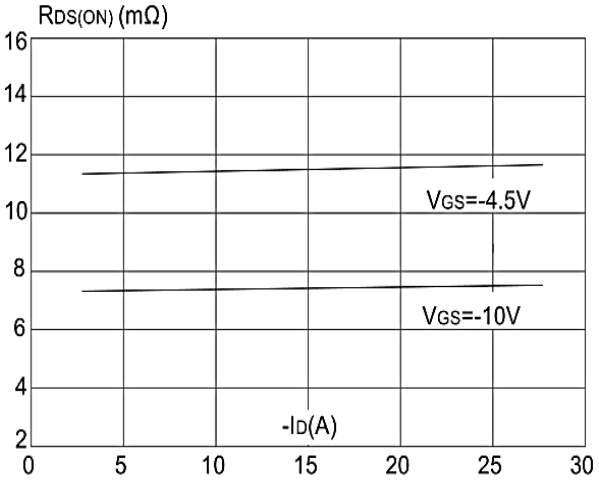


Figure 3:On-resistance vs. Drain Current

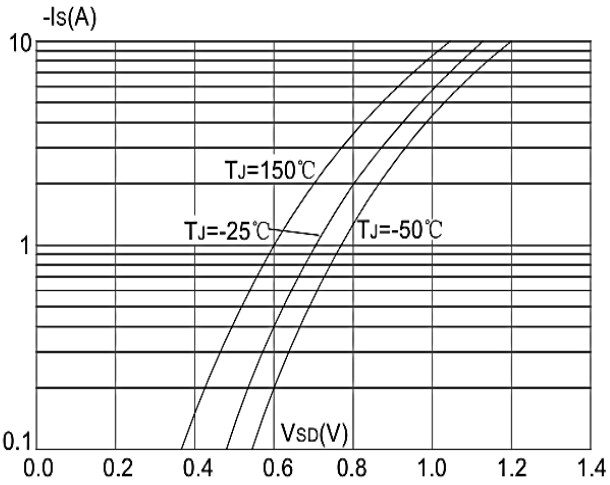


Figure 4: Body Diode Characteristics

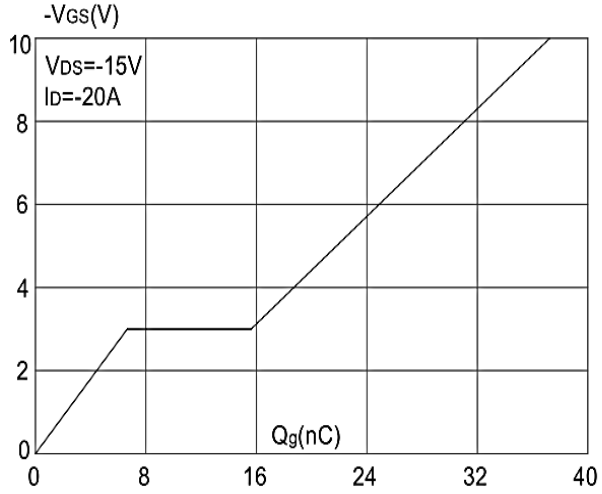


Figure 5: Gate Charge Characteristics

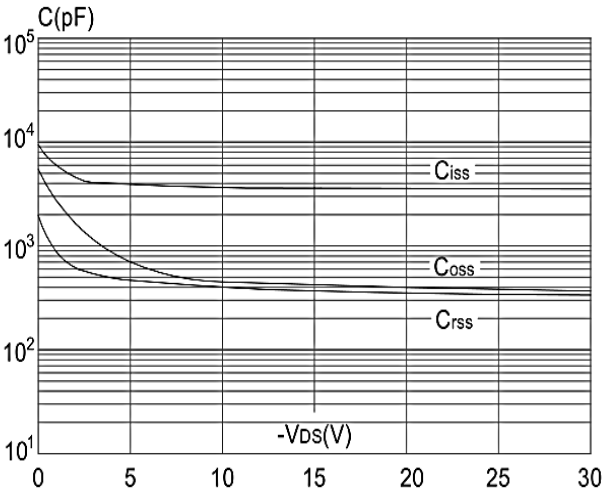


Figure 6: Capacitance Characteristics

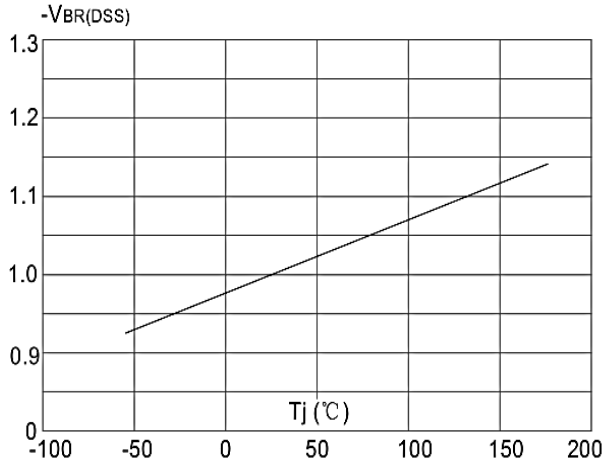


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

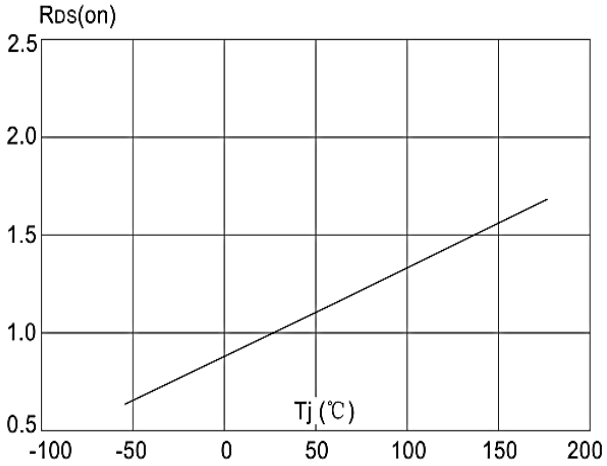


Figure 8: Normalized on Resistance vs. Junction Temperature

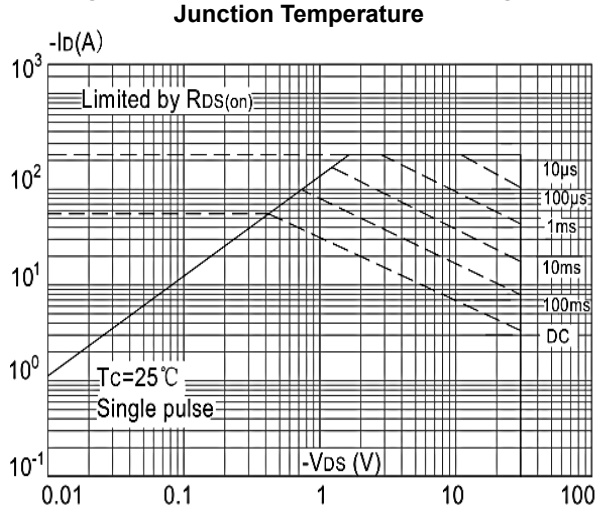


Figure 9: Maximum Safe Operating Area

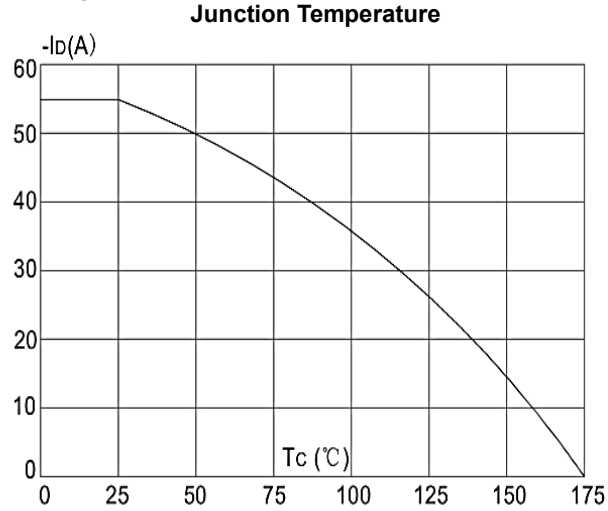


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

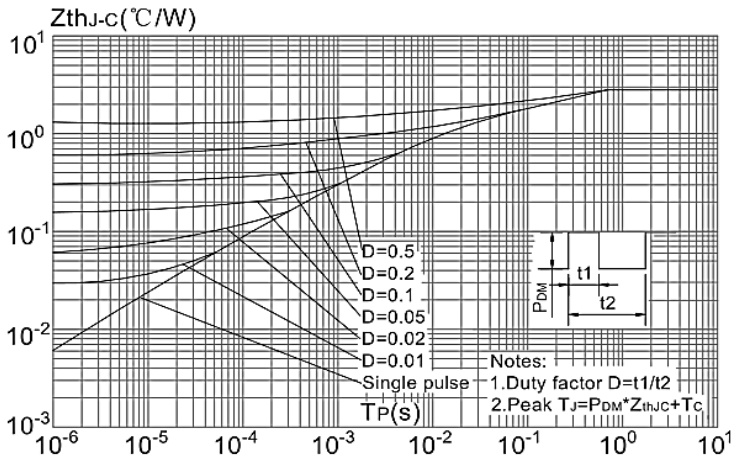
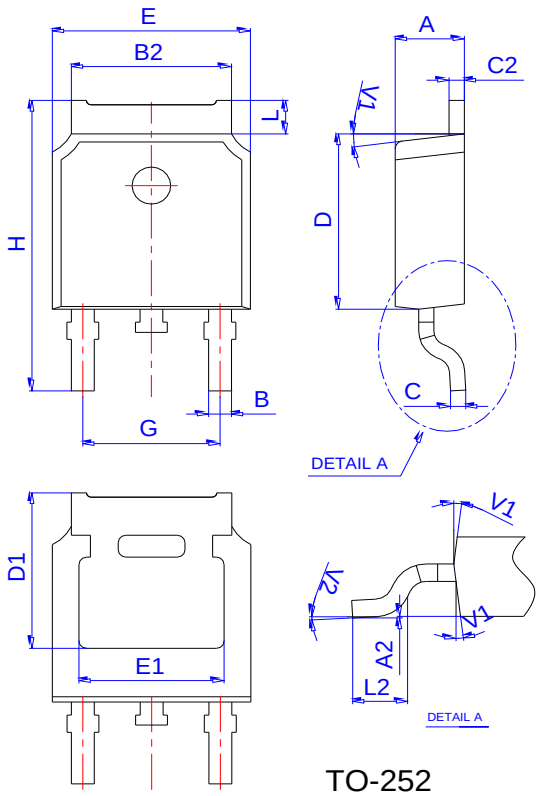


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

-30V P-Channel Enhancement Mode MOSFET

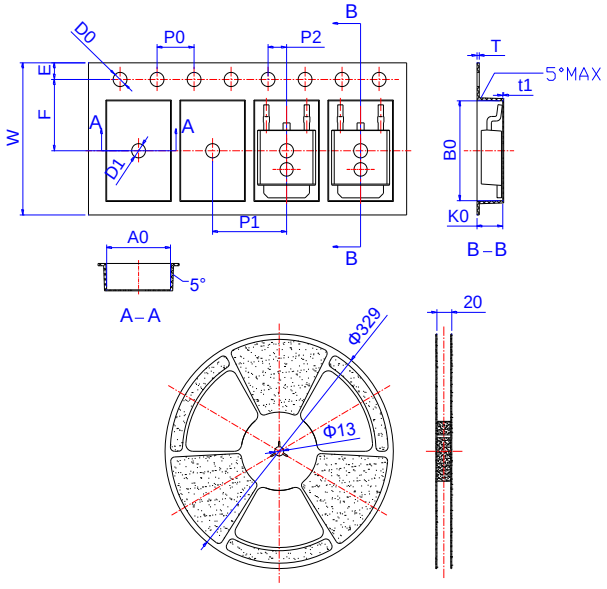
Package Mechanical Data:TO-252-3L



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Spectification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

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-30V P-Channel Enhancement Mode MOSFET

Edition	Date	Change
Rve3.8	2021/1/10	Initial release
Rve3.9	2022/3/1	Reduce internal RDS